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拓電半導體

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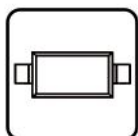
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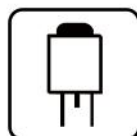
電源管理



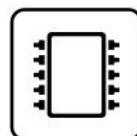
顯示驅動



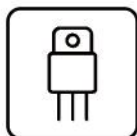
二三極管



LDO穩壓器



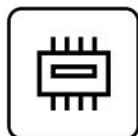
觸摸芯片



MOS管



運算放大器



存儲芯片



MCU



串口通信

MMBT3904 1AM

產品規格說明書

MMBT3904 1AM NPN Plastic-Encapsulate Transistors

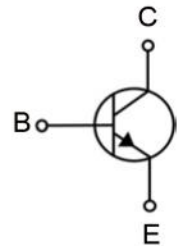
Features

- Collector Current: $I_C=0.2A$
- Power Dissipation of 200mw

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
MMBT3904	SOT-23	1AM	3000

SOT-23



Maxmim Ratings ($T_a=25^{\circ}C$ unless otherwise noted)

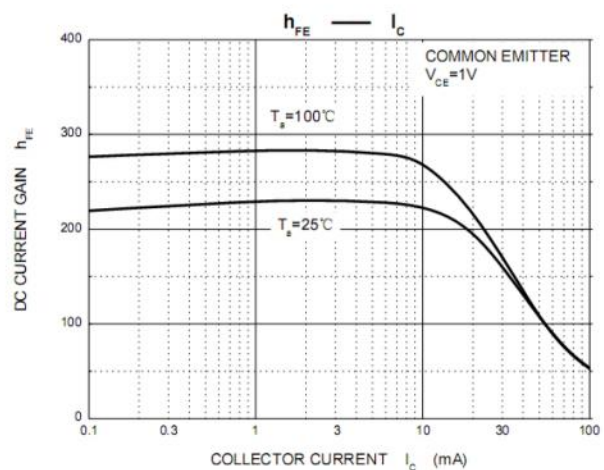
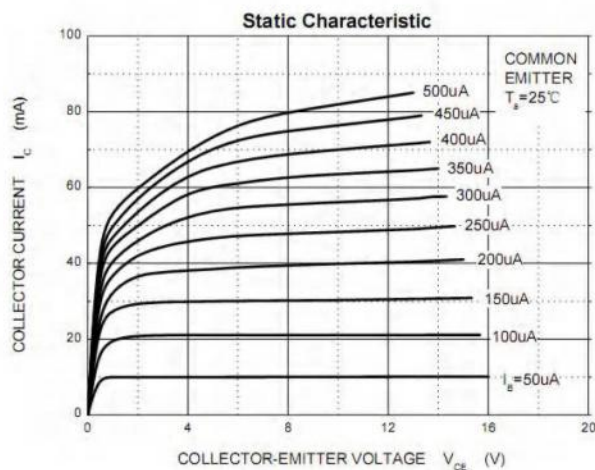
Parameter	Symbol	Limit	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current	I_C	200	mA
Collector Power Dissipation	P_C	200	mW
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	625	$^{\circ}C/W$
Junction Temperature	T_J	150	$^{\circ}C$
Storage Temperature	T_{stg}	-55~+150	$^{\circ}C$

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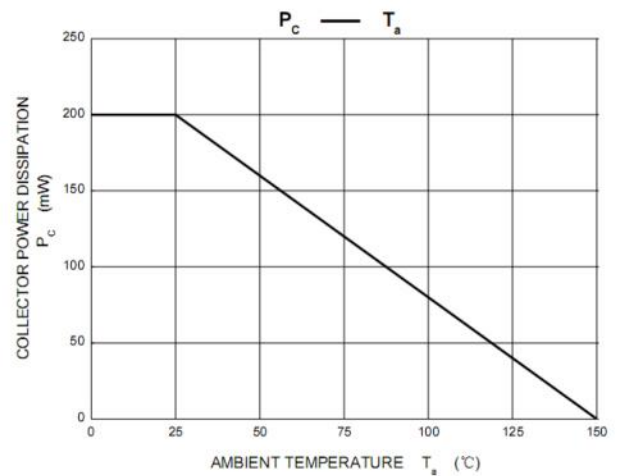
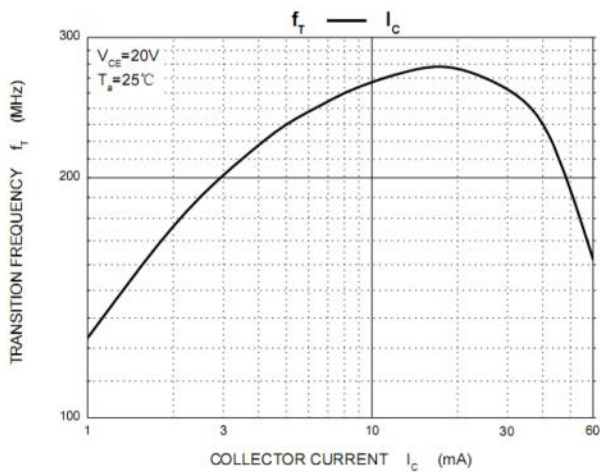
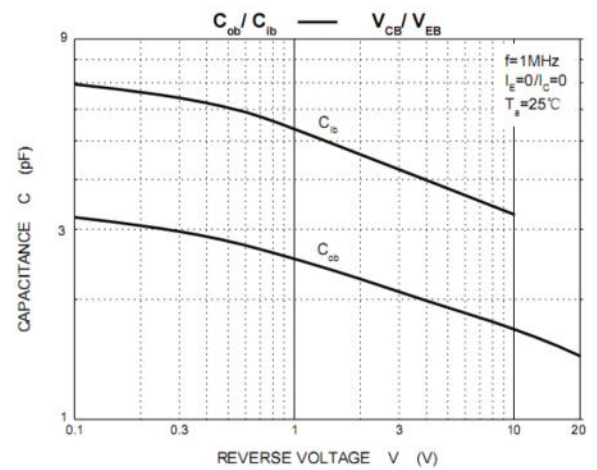
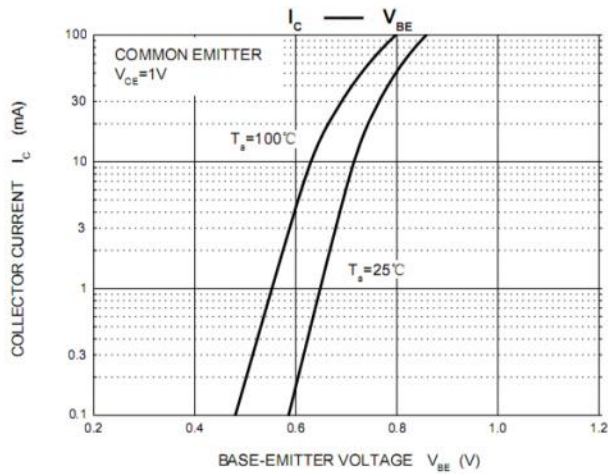
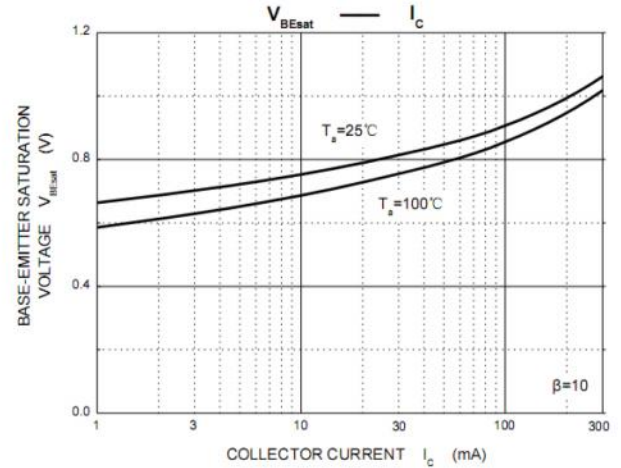
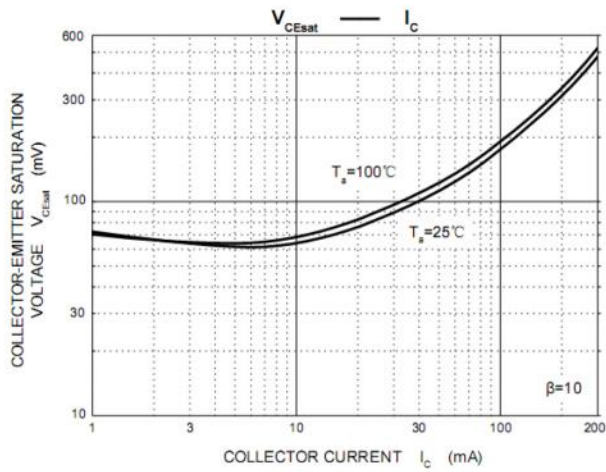
Electrcal Charcteristics (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	6			V
Collector cut-off current	I_{CEX}	$V_{CE}=30V, V_{EB(off)}=3V$			50	nA
Collector cut-off current	I_{CBO}	$V_{CB}=60V, I_E=0$			100	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$			100	nA
DC current gain	$h_{FE(1)}$	$V_{CE}=1V, I_C=10mA$	100		300	
	$h_{FE(2)}$	$V_{CE}=1V, I_C=50mA$	60			
	$h_{FE(3)}$	$V_{CE}=1V, I_C=100mA$	30			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=50mA, I_B=5mA$			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=50mA, I_B=5mA$			0.95	V
Transition frequency	f_T	$V_{CE}=20V, I_C=10mA, f=100MHz$	300			MHz
Delay time	t_d	$V_{CC}=3V, V_{BE(off)}=-0.5V, I_C=10mA, I_{B1}=1mA$			35	ns
Rise time	t_r	$V_{CC}=3V, V_{BE(off)}=-0.5V, I_C=10mA, I_{B1}=1mA$			35	ns
Storage time	t_s	$V_{CC}=3V, I_C=10mA, I_{B1}=I_{B2}=1mA$			200	ns
Fall time	t_f	$V_{CC}=3V, I_C=10mA, I_{B1}=I_{B2}=1mA$			50	ns

Typical Characteristics

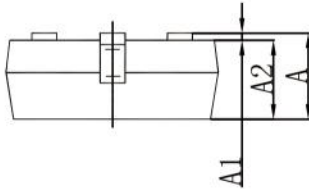
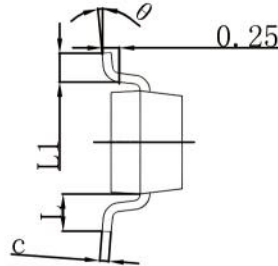
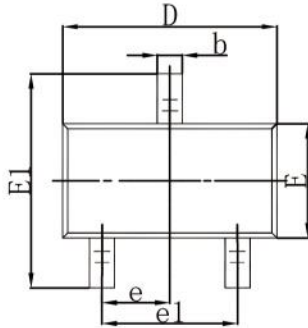


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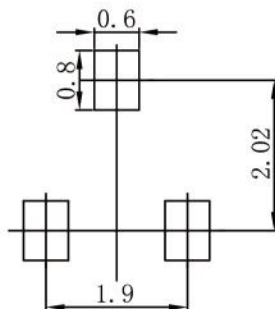
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SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.